

## FNK N-Channel Enhancement Mode Power MOSFET

### Description

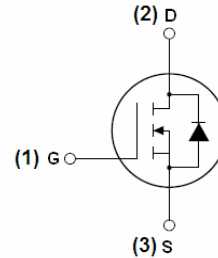
The FNK01N15D uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

### General Features

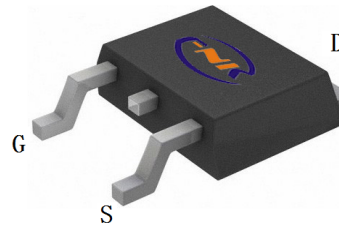
- $V_{DS} = 100V, I_D = 150A$   
 $R_{DS(ON)} < 5.7m\Omega @ V_{GS} = 10V$  (Typ: 5.0m $\Omega$ )
- High density cell design for ultra low  $R_{dson}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high  $E_{AS}$
- Excellent package for good heat dissipation

### Application

- Power switching application
- Load switching
- Uninterruptible power supply



Schematic diagram



To-263 Top View

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
FNK01N15D	FNK01N15D	TO-263	-	-	-

### Absolute Maximum Ratings ( $T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	150	A
Drain Current-Continuous( $T_C = 100^\circ C$ )	$I_D(100^\circ C)$	113	A
Pulsed Drain Current	$I_{DM}$	580	A
Maximum Power Dissipation	$P_D$	370	W
Derating factor		2.5	W/ $^\circ C$
Single pulse avalanche energy <sup>(Note 5)</sup>	$E_{AS}$	433	mJ

Parameter	Symbol	Limit	Unit
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175	°C

### Thermal Characteristic

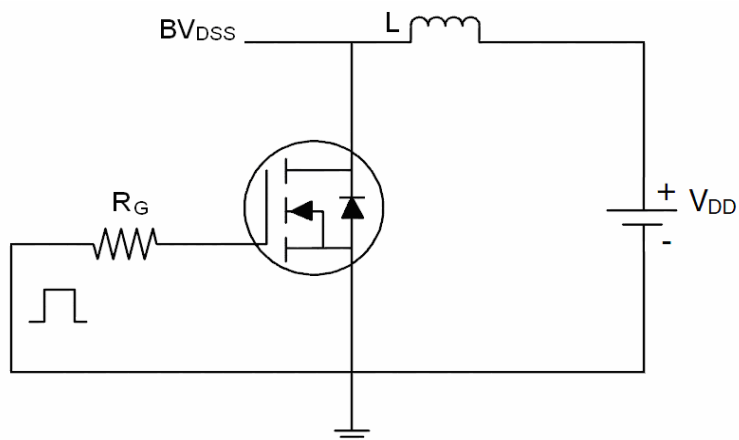
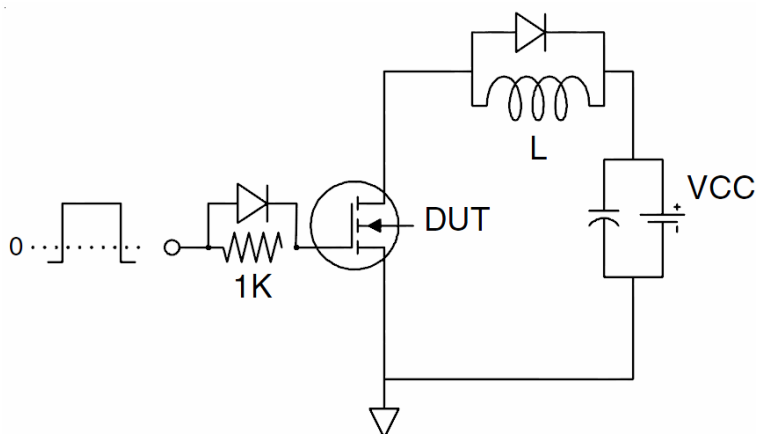
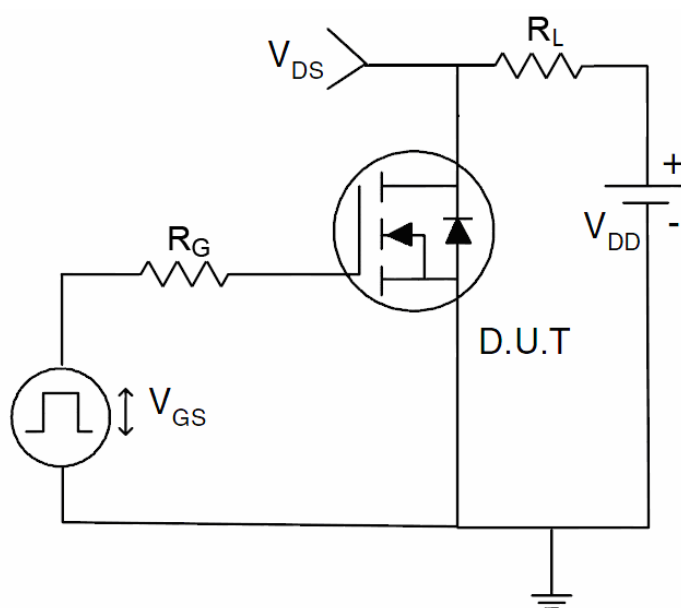
Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	$R_{\theta JC}$	0.4	°C/W
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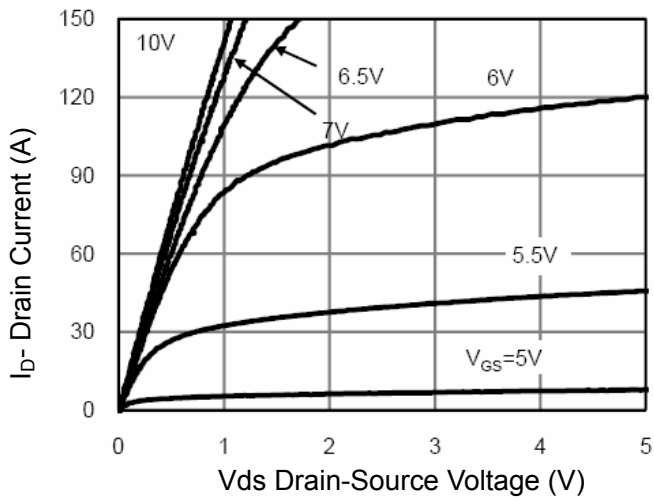
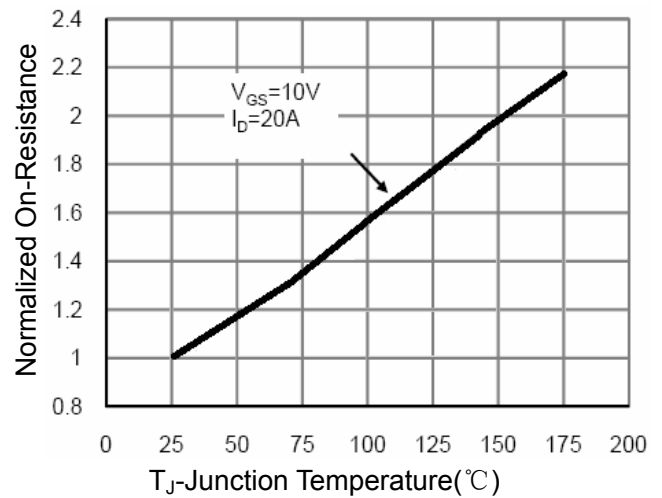
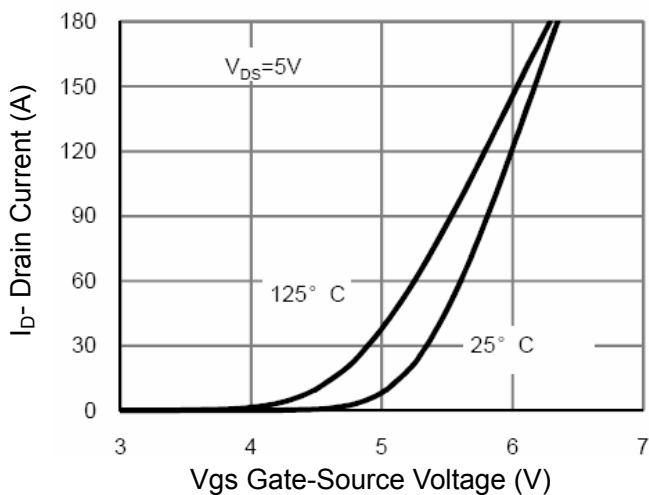
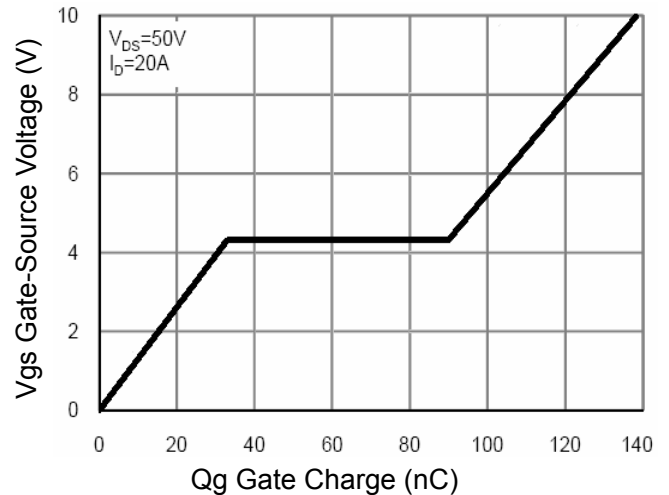
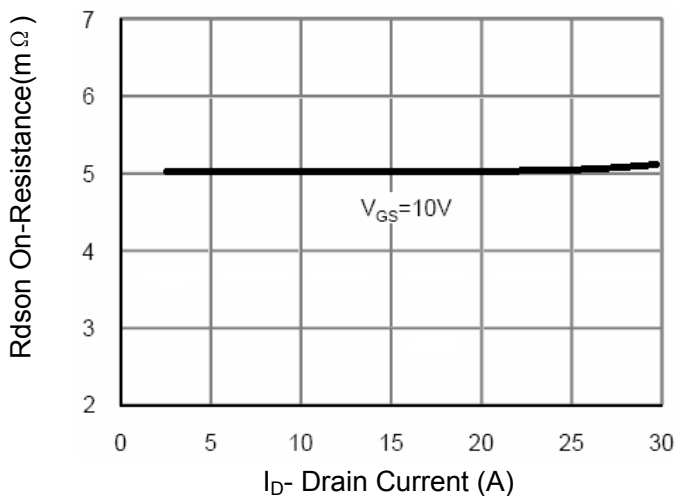
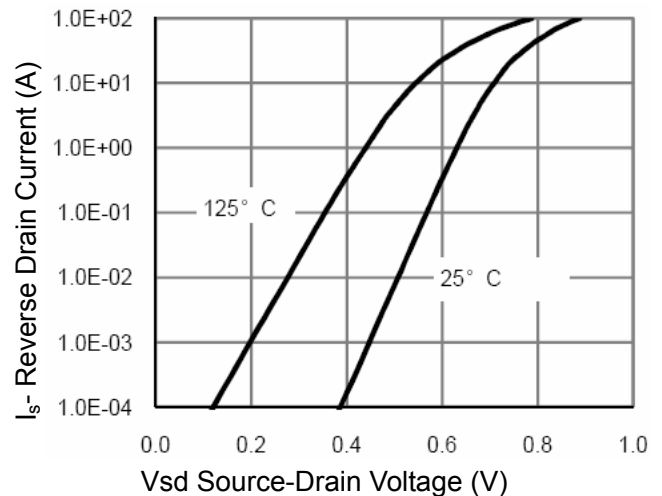
### Electrical Characteristics ( $T_C=25^\circ\text{C}$ unless otherwise noted)

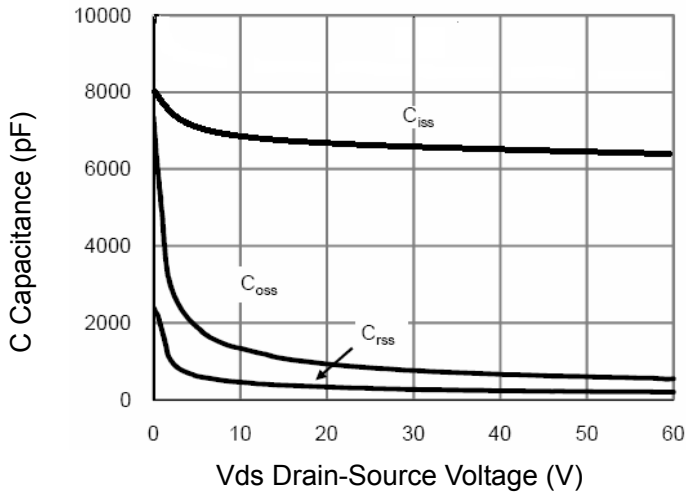
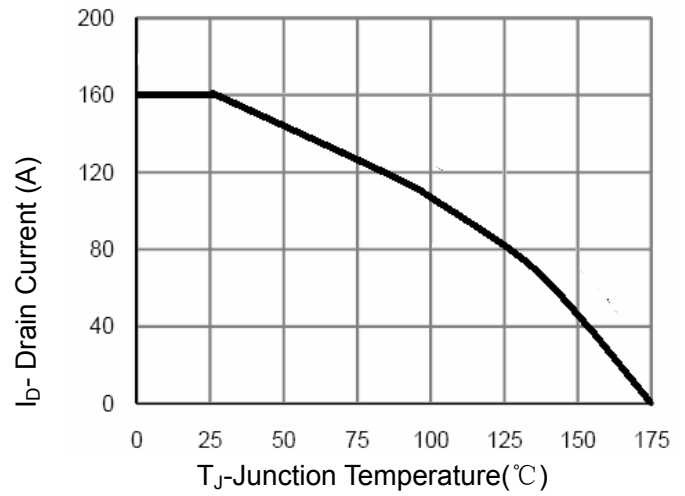
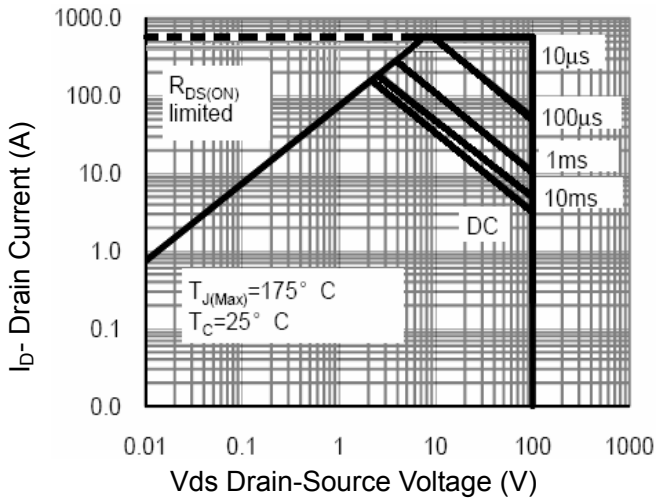
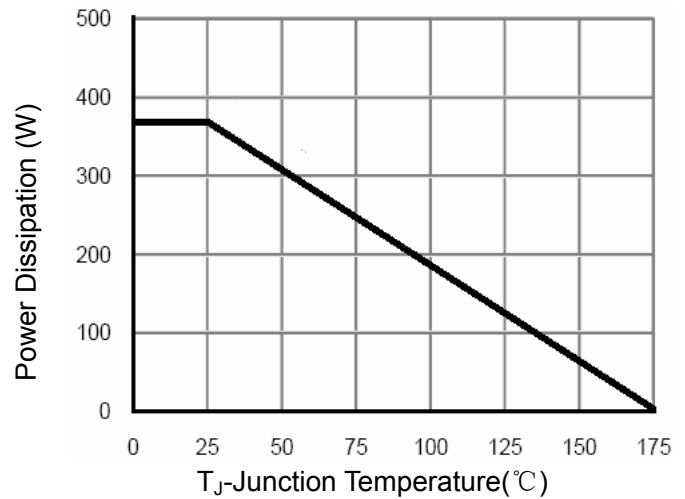
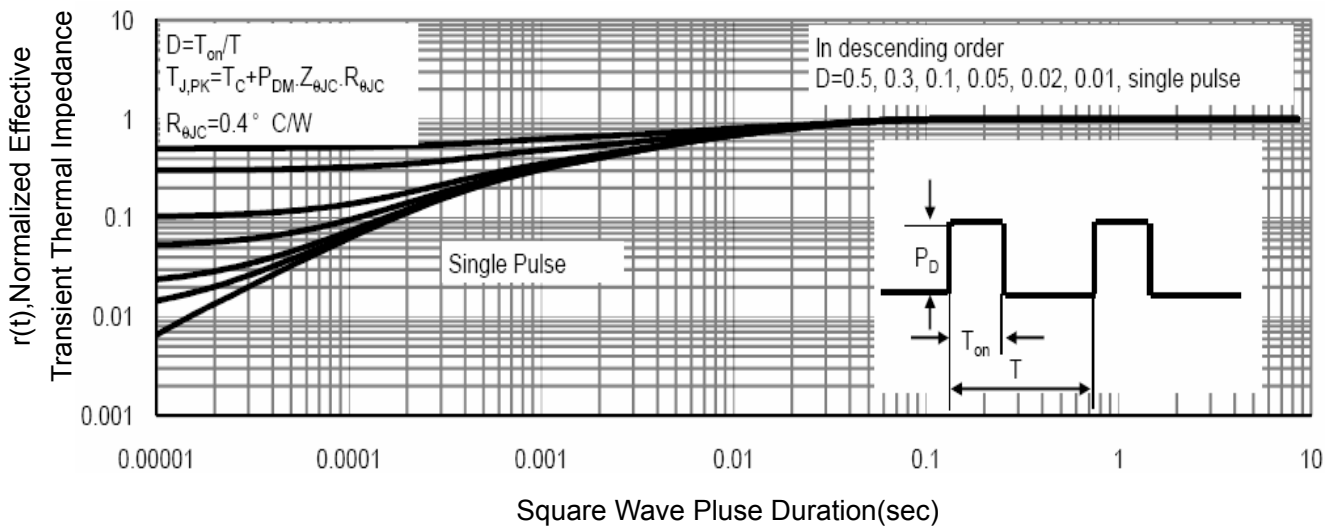
Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	100	110	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=100V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	±100	nA
<b>On Characteristics</b> <sup>(Note 3)</sup>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2	2.8	4	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$	-	5.0	5.7	mΩ
Forward Transconductance	$g_{FS}$	$V_{DS}=5V, I_D=20A$	70	-	-	S
<b>Dynamic Characteristics</b> <sup>(Note 4)</sup>						
Input Capacitance	$C_{iss}$	$V_{DS}=25V, V_{GS}=0V,$ $F=1.0\text{MHz}$	-	6470	-	PF
Output Capacitance	$C_{oss}$		-	690	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	430	-	PF
<b>Switching Characteristics</b> <sup>(Note 4)</sup>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=50V, R_L=2.5\Omega$ $V_{GS}=10V, R_{GEN}=3\Omega$	-	28	-	nS
Turn-on Rise Time	$t_r$		-	22	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	43.5	-	nS
Turn-Off Fall Time	$t_f$		-	14.5	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=50V, I_D=20A,$ $V_{GS}=10V$	-	139	-	nC
Gate-Source Charge	$Q_{gs}$		-	34	-	nC
Gate-Drain Charge	$Q_{gd}$		-	56	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage <sup>(Note 3)</sup>	$V_{SD}$	$V_{GS}=0V, I_S=20A$	-	0.85	1.2	V
Diode Forward Current <sup>(Note 2)</sup>	$I_S$		-	-	160	A
Reverse Recovery Time	$t_{rr}$	$T_J = 25^\circ\text{C}, I_F = 20A$ $di/dt = 100A/\mu s$ <sup>(Note 3)</sup>	-	60	90	nS
Reverse Recovery Charge	$Q_{rr}$		-	177	200	nC

### Notes:

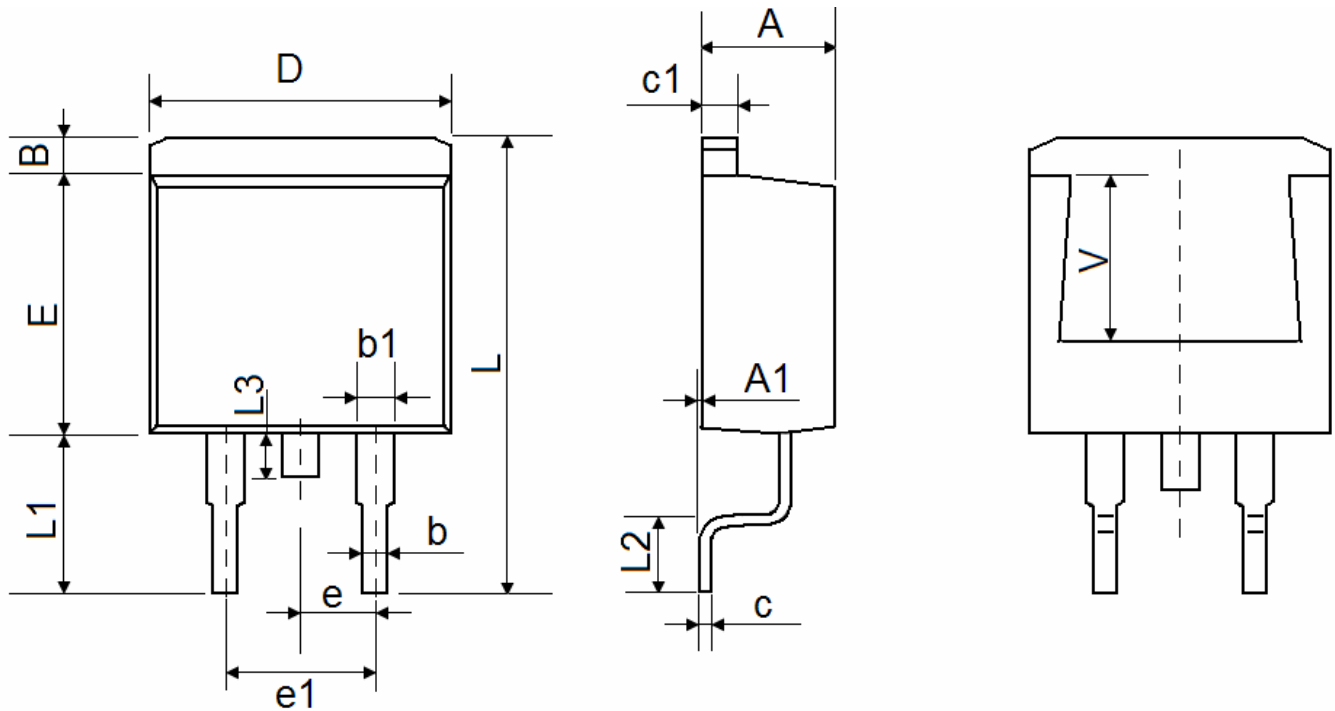
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production
5. EAS condition:  $T_J=25^\circ\text{C}, V_{DD}=50V, V_G=10V, L=0.5\text{mH}, R_g=25\Omega$

**Test Circuit**
**1) E<sub>AS</sub> test Circuit**

**2) Gate charge test Circuit**

**3) Switch Time Test Circuit**


**Typical Electrical and Thermal Characteristics (Curves)**

**Figure 1 Output Characteristics**

**Figure 4 Rdson-Junction Temperature**

**Figure 2 Transfer Characteristics**

**Figure 5 Gate Charge**

**Figure 3 Rdson- Drain Current**

**Figure 6 Source- Drain Diode Forward**


**Figure 7 Capacitance vs Vds**

**Figure 9  $I_D$  Current- Junction Temperature**

**Figure 8 Safe Operation Area**

**Figure 10 Power De-rating**

**Figure 11 Normalized Maximum Transient Thermal Impedance**

## TO-263 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.470	4.670	0.176	0.184
A1	0.000	0.150	0.000	0.006
B	1.170	1.370	0.046	0.054
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.310	0.530	0.012	0.021
c1	1.170	1.370	0.046	0.054
D	10.010	10.310	0.394	0.406
E	8.500	8.900	0.335	0.350
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
L	15.050	15.450	0.593	0.608
L1	5.080	5.480	0.200	0.216
L2	2.340	2.740	0.092	0.108
L3	1.300	1.700	0.051	0.067
V	5.600 REF		0.220 REF	

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